WESTCODE

An IXYS Company

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Data Sheet Issue:- A1

Provisional Data

Medium Voltage Thyristor

Type K0620Q#600 to K0620Q#650

Development Type No. KX265Q#600-650

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	6000-6500	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	6000-6500	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	6100-6600	V

	OTHER RATINGS		MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current, T_{sink}=55°C, (note 2)		620	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 2)		430	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 3)		260	A
$I_{T(RMS)}$	Nominal RMS on-state current, T_{sink}=25°C, (note 2)		1215	A
$I_{T(d.c.)}$	D.C. on-state current, T_{sink}=25°C, (note 4)		1075	A
I_{TSM}	Peak non-repetitive surge t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)		7250	A
I_{TSM2}	Peak non-repetitive surge t_p=10ms, $V_{rm}\leq$10V, (note 5)		8000	A
I^2t	I^2t capacity for fusing t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)		263×10^3	A^2s
I^2t	I^2t capacity for fusing t_p=10ms, $V_{rm}\leq$10V, (note 5)		320×10^3	A^2s
$(di/dt)_{cr}$	Critical rate of rise of on-state current, (Note 6)	continuous, 50Hz	100	A/µs
		repetitive, 50Hz, 60s	200	
		non-repetitive	700	
V_{RGM}	Peak reverse gate voltage		5	V
$P_{G(AV)}$	Mean forward gate power		2	W
P_{GM}	Peak forward gate power		30	W
$T_{j\ op}$	Operating temperature range		-40 to +125	°C
T_{stg}	Storage temperature range		-40 to +150	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.
2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
4) Double side cooled.
5) Half-sinewave, 125°C T_j initial.
6) V_D=67% V_{DRM}, I_{FG}=2A, $t_r\leq$0.5µs, T_{case}=125°C.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{TM}	Maximum peak on-state voltage	2.80	-	3.00	I_{TM}=1000A	V
V_{TM}	Maximum peak on-state voltage	-	-	4.15	I_{TM}=1800A	V
V_{T0}	Threshold voltage	-	-	1.54		V
r_T	Slope resistance	-	-	1.45		mΩ
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	1000	-	-	V_D=80% V_{DRM}, linear ramp, gate o/c	V/µs
I_{DRM}	Peak off-state current	-	-	50	Rated V_{DRM}	mA
I_{RRM}	Peak reverse current	-	-	50	Rated V_{RRM}	mA
V_{GT}	Gate trigger voltage	-	-	1.80	T_j=25°C. V_D=10V, I_T=3A	V
I_{GT}	Gate trigger current	-	-	300		mA
V_{GD}	Gate non-trigger voltage	-	-	0.25	Rated V_{DRM}	V
I_H	Holding current	-	-	1000	T_j=25°C	mA
t_{gd}	Gate-controlled turn-on delay time	-	0.5	1.5	V_D=67% V_{DRM}, I_T=1000A, di/dt=10A/µs, I_{FG}=2A, t_r=0.5µs, T_j=25°C	µs
t_{gt}	Turn-on time	-	2.0	5.0		µs
Q_{rr}	Recovered charge	3400	-	4200	I_{TM}=2000A, t_p=1000µs, di/dt=10A/µs, V_r=100V	µC
Q_{ra}	Recovered charge, 50% chord	-	1800	-		µC
I_{rm}	Reverse recovery current	125	-	140		A
t_{rr}	Reverse recovery time, 50% chord	-	27	-		µs
t_q	Turn-off time	700	-	-	I_{TM}=2000A, t_p=1000µs, di/dt=10A/µs, V_r=100V, V_{dr}=27%V_{DRM}, dV_{dr}/dt=20V/µs	µs
		1000	-	-	I_{TM}=2000A, t_p=1000µs, di/dt=10A/µs, V_r=100V, V_{dr}=67%V_{DRM}, dV_{dr}/dt=200V/µs	
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.030	Double side cooled	K/W
		-	-	0.057	Anode side cooled	K/W
		-	-	0.063	Cathode side cooled	K/W
F	Mounting force	16	-	20		kN
W_t	Weight	-	330	-	Housing option QA	g
		-	420	-	Housing option QE	g

Notes:-
1) Unless otherwise indicated T_j=125°C.
2) For other clamp forces consult factory.

Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V_{DRM} V_{DSM} V_{RRM} V	V_{RSM} V	V_D V_R DC V
60	6000	6100	3000
62	6200	6300	3100
64	6400	6500	3200
65	6500	6600	3250

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

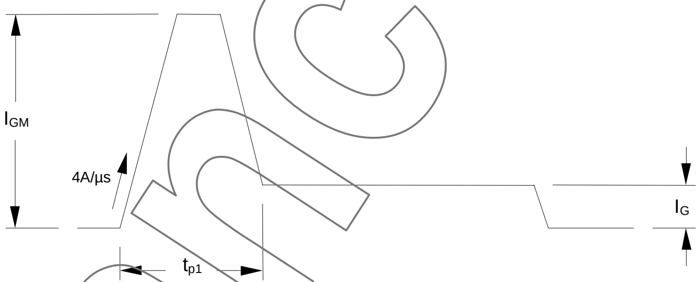
A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_j below 25°C.

4.0 Repetitive dv/dt

Standard dv/dt is 1000V/µs.

5.0 Gate Drive

The nominal requirement for a typical gate drive is illustrated below. An open circuit voltage of at least 30V is assumed. This gate drive must be applied when using the full di/dt capability of the device.



The magnitude of I_{GM} should be between five and ten times I_{GT}, which is shown on page 2. Its duration (t_{p1}) should be 20µs or sufficient to allow the anode current to reach ten times I_L, whichever is greater. Otherwise, an increase in pulse current could be needed to supply the necessary charge to trigger. The 'back-porch' current I_G should remain flowing for the same duration as the anode current and have a magnitude in the order of 1.5 times I_{GT}.

6.0 Frequency Ratings

The curves illustrated in figures 17 & 18 are for guidance only and are superseded by the maximum ratings shown on page 1. For operation above line frequency, please consult the factory for assistance.

7.0 Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 700A/µs at any time during turn-on on a non-repetitive basis. For repetitive performance, the on-state rate of rise of current must not exceed 200A/µs at any time during turn-on. Note that these values of rate of rise of current apply to the total device current including that from any local snubber network.

8.0 Square wave frequency ratings

These ratings are given for load component rate of rise of on-state current of 50A/µs.

9.0 Computer Modelling Parameters

9.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{V_{T0}^{\,2} + 4 \cdot ff^{2} \cdot r_T \cdot W_{AV}}}{2 \cdot ff^{2} \cdot r_T}$$

and:

$$W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_{Hs}$$

Where V_{T0}=1.54V, r_T=1.45Ω,

R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.0326	0.0322	0.0318	0.0314	0.0310	0.0305	0.0300
Square wave Cathode Side Cooled	0.0666	0.0661	0.0657	0.0653	0.0645	0.0635	0.0630
Sine wave Double Side Cooled	0.0323	0.0317	0.0313	0.0310	0.0305		
Sine wave Cathode Side Cooled	0.0662	0.0656	0.0652	0.0648	0.0637		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.464	2.449	2	1.732	1.414	1.149	1
Sine wave	3.98	2.778	2.22	1.879	1.57		

9.2 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

Where p = *1* to *n*, *n* is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- r_t = Thermal resistance at time t.
- r_p = Amplitude of p_{th} term.
- τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below:

D.C. Double Side Cooled			
Term	1	2	3
r_p	0.01618388	8.751247×10^{-3}	4.004227×10^{-3}
τ_p	0.6893478	0.09708551	0.01622755

D.C. Cathode Side Cooled			
Term	1	2	3
r_p	0.0414664	0.01383440	4.721539×10^{-3}
τ_p	4.635928	0.01748947	0.01644571

9.3 Calculating V_T using ABCD Coefficients

The on-state characteristic I_T vs. V_T, on page 6 is represented in two ways;

(i) the well established V_{T0} and r_T tangent used for rating purposes and

(ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_T in terms of I_T given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for the hot and cold characteristics. The resulting values for V_T agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients	
A	2.923185	A	2.206732
B	-0.3210737	B	-0.1958308
C	0.868939×10^{-4}	C	1.169098×10^{-3}
D	0.03709766	D	0.03090623

10.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

11.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{rm} chord as shown in Fig. 1

(ii) Q_{rr} is based on a 150µs integration time i.e.

$$Q_{rr} = \int_0^{150\mu s} i_{rr}.dt$$

(iii)

$$K\ Factor = \frac{t_1}{t_2}$$

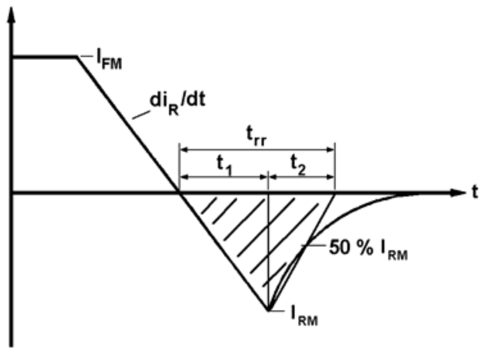


Fig. 1

12.0 Duty cycle lines

The 100% duty cycle is represented on the frequency ratings by a straight line. Other duties can be included as parallel to the first.

Curves

Figure 1 – On-state characteristics of Limit device

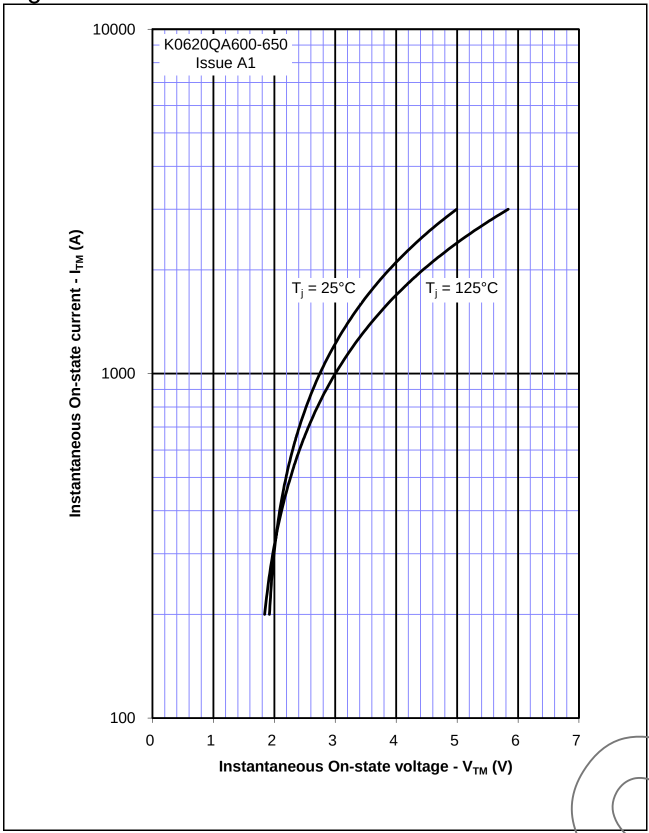


Figure 2 – Transient thermal impedance

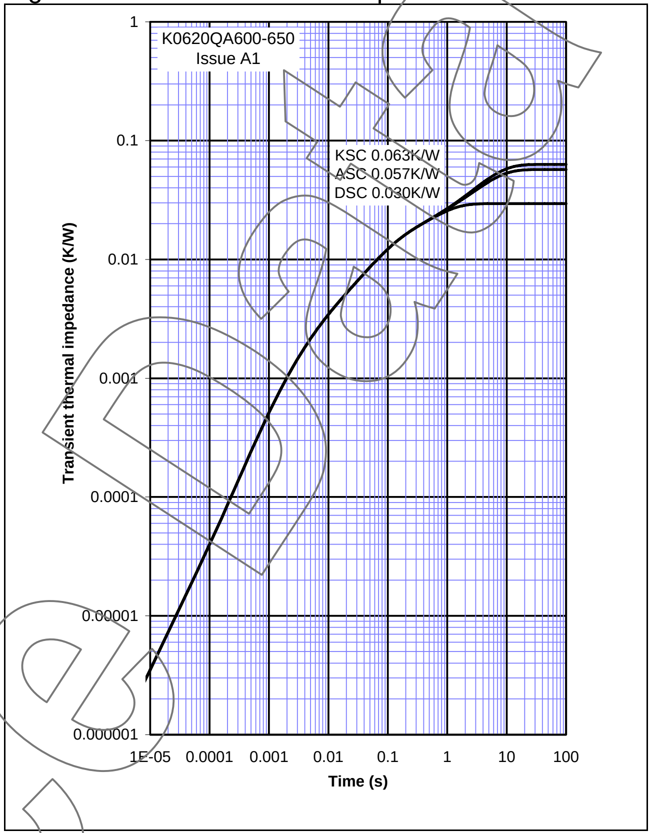


Figure 3 – Gate characteristics – Trigger limits

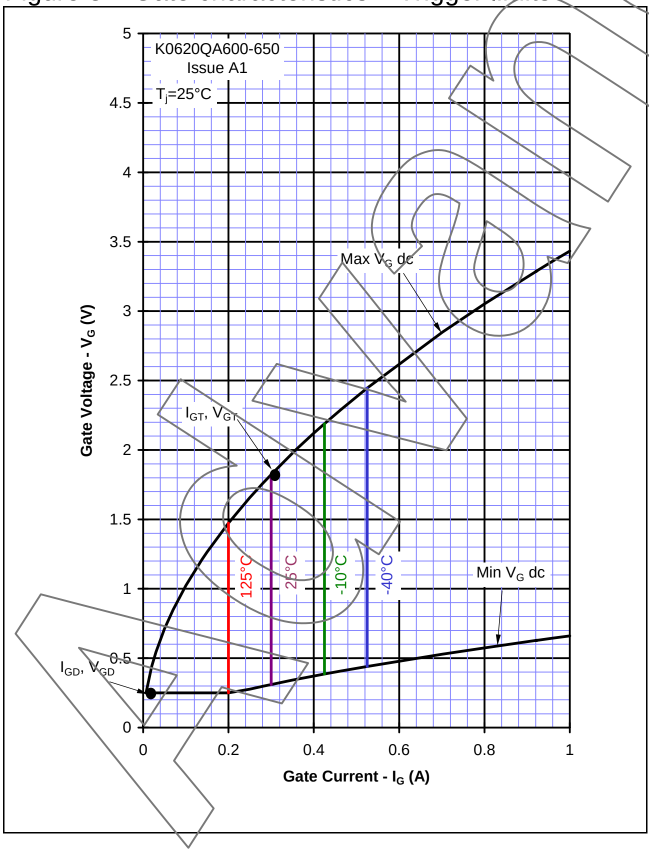


Figure 4 – Gate characteristics – Power curves

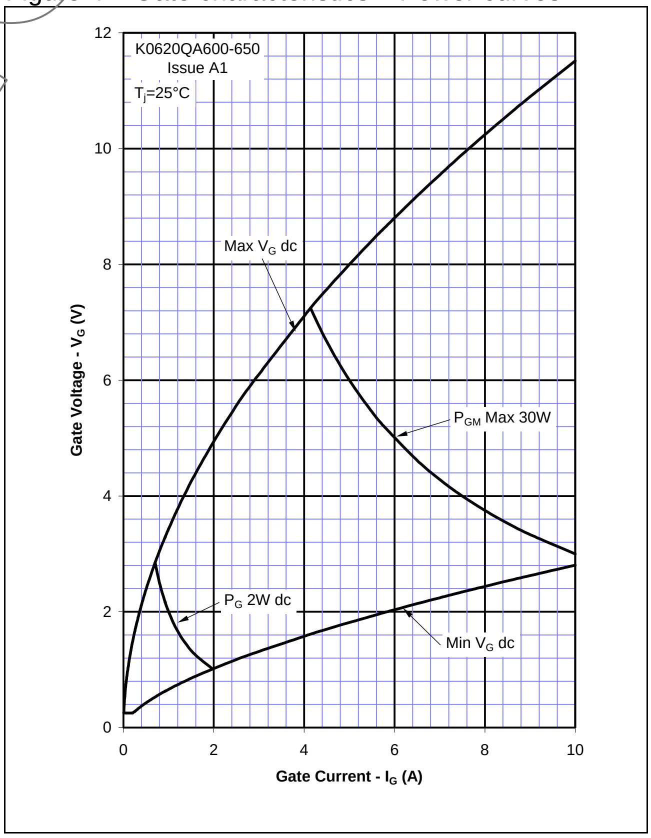


Figure 5 – Total recovered charge, Q_{rr}

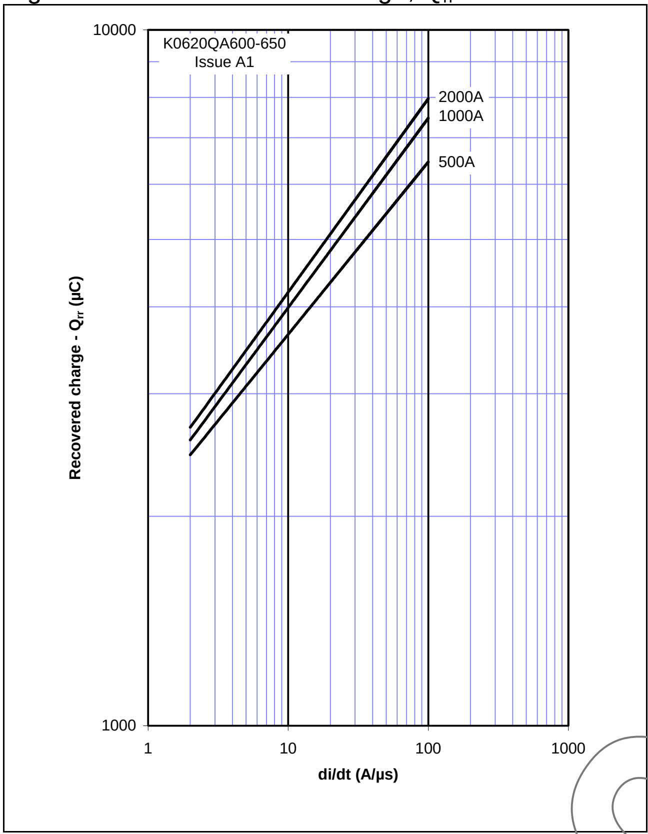


Figure 6 – Recovered charge, Q_{ra} (50% chord)

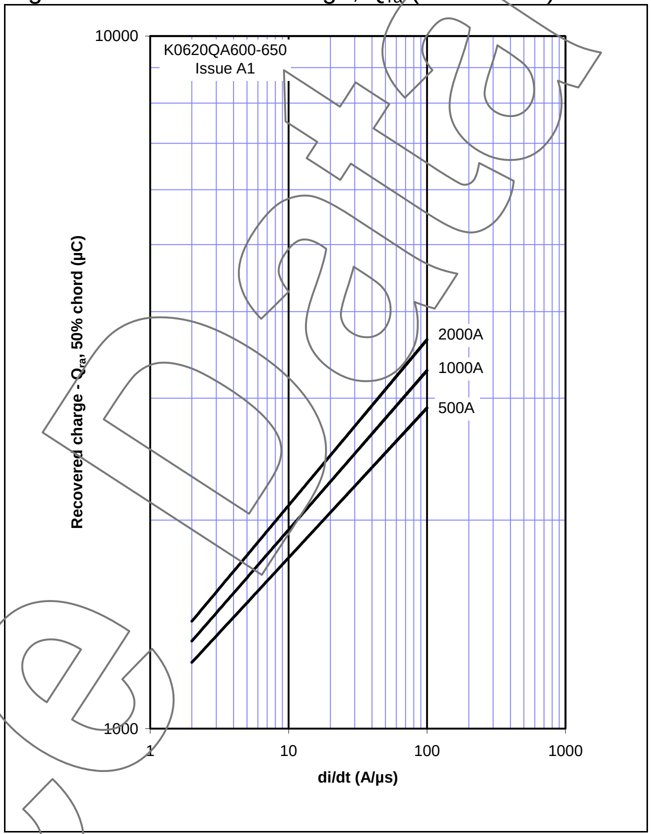


Figure 7 – Peak reverse recovery current, I_{rm}

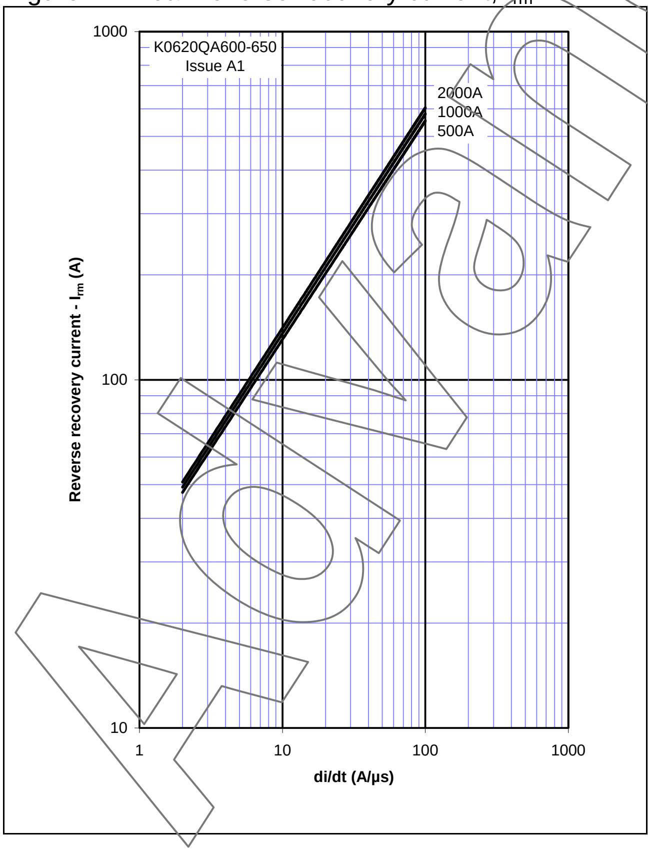


Figure 8 – Maximum recovery time, t_{rr} (50% chord)

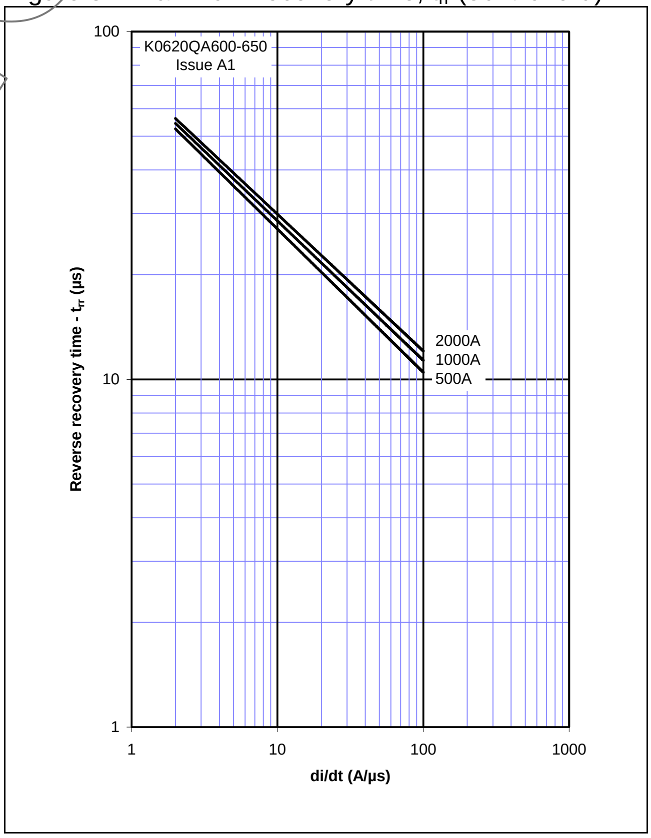


Figure 9 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

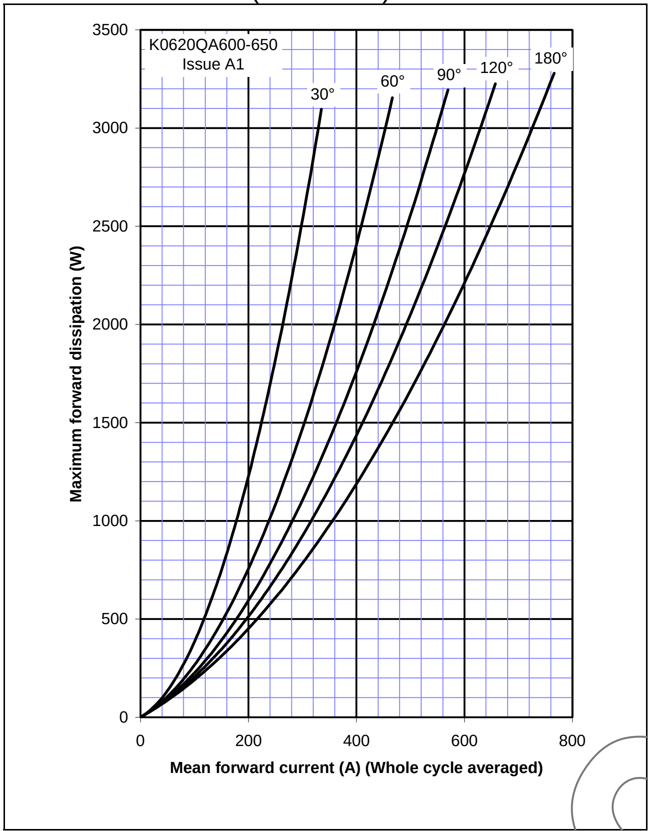


Figure 10 – On-state current vs. Heatsink temperature – Double Side Cooled (Sine wave)

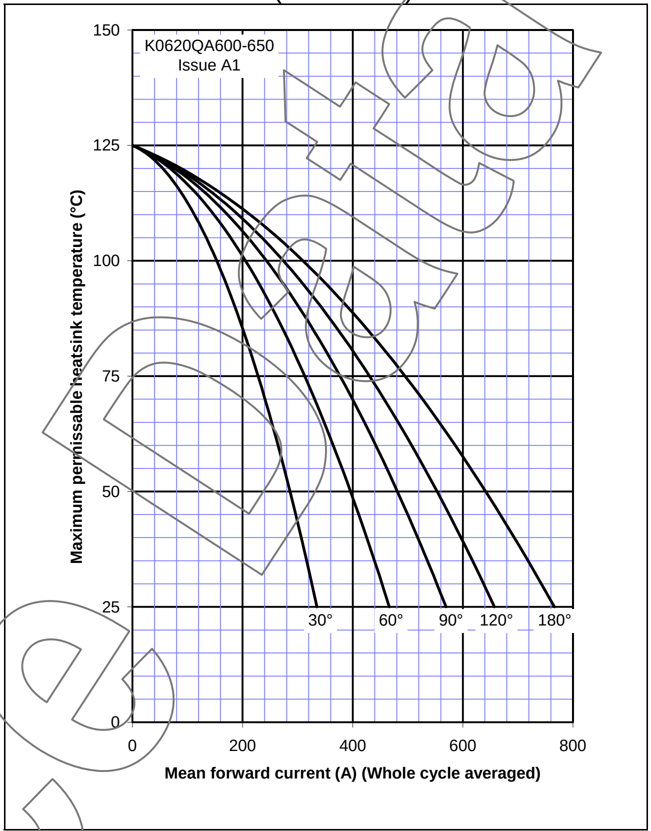


Figure 11 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

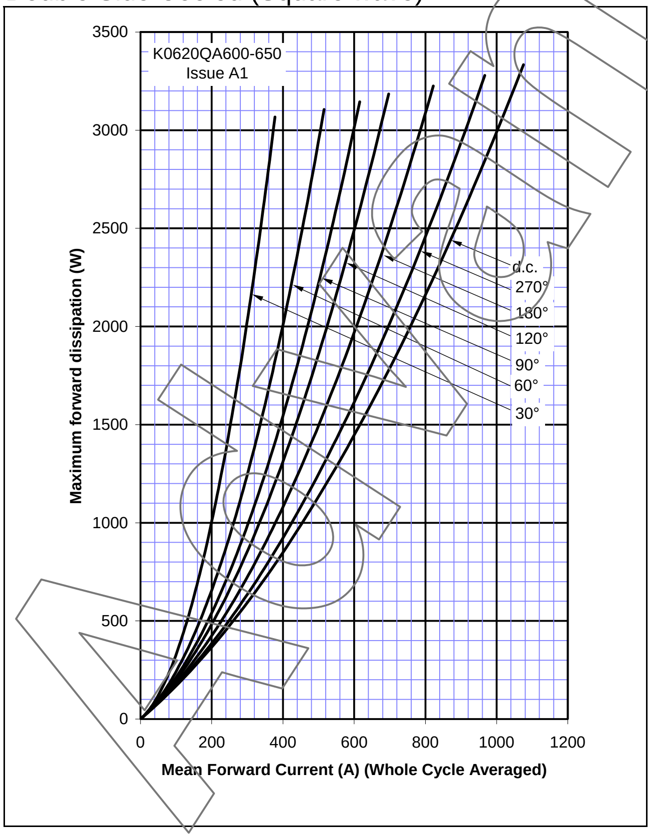


Figure 12 – On-state current vs. Heatsink temperature – Double Side Cooled (Square wave)

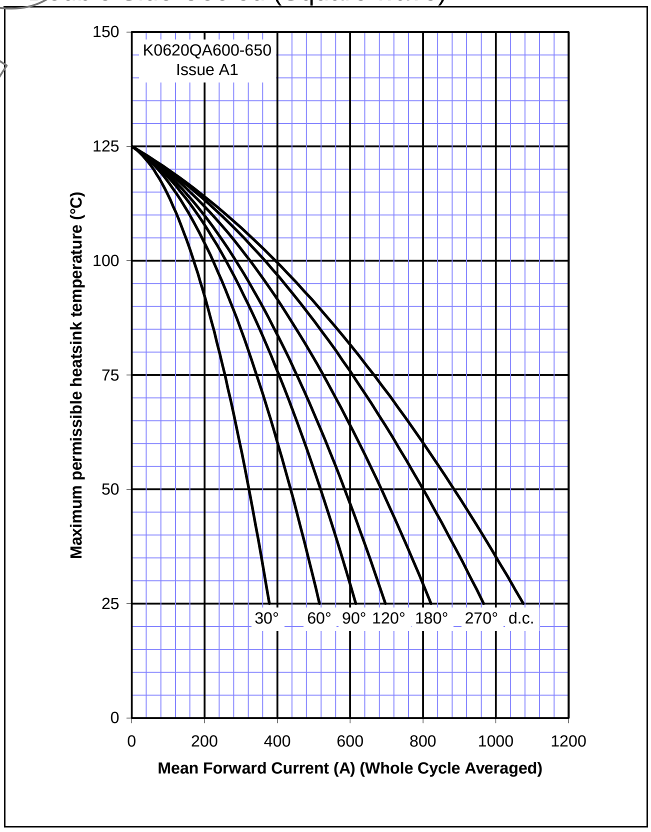


Figure 13 – On-state current vs. Power dissipation – Cathode Side Cooled (Sine wave)

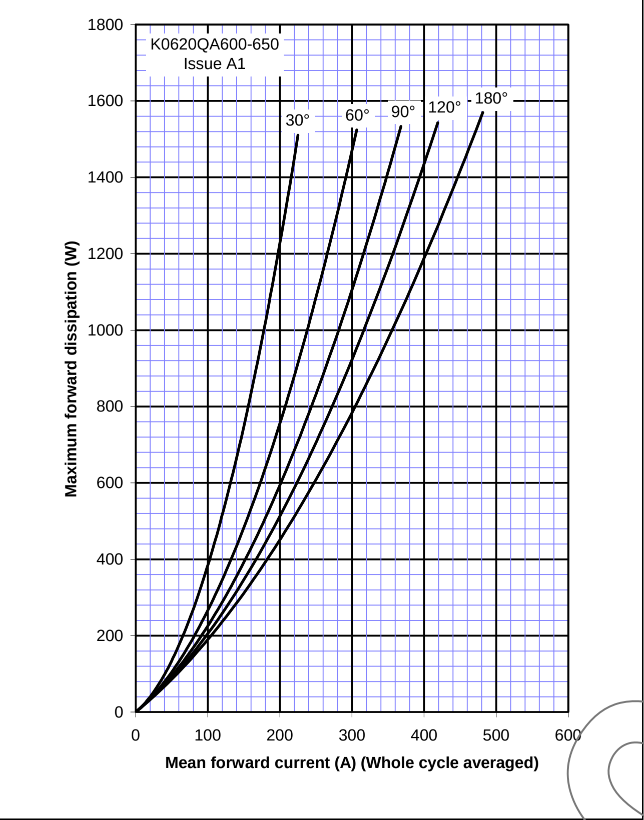


Figure 14 – On-state current vs. Heatsink temperature – Cathode Side Cooled (Sine wave)

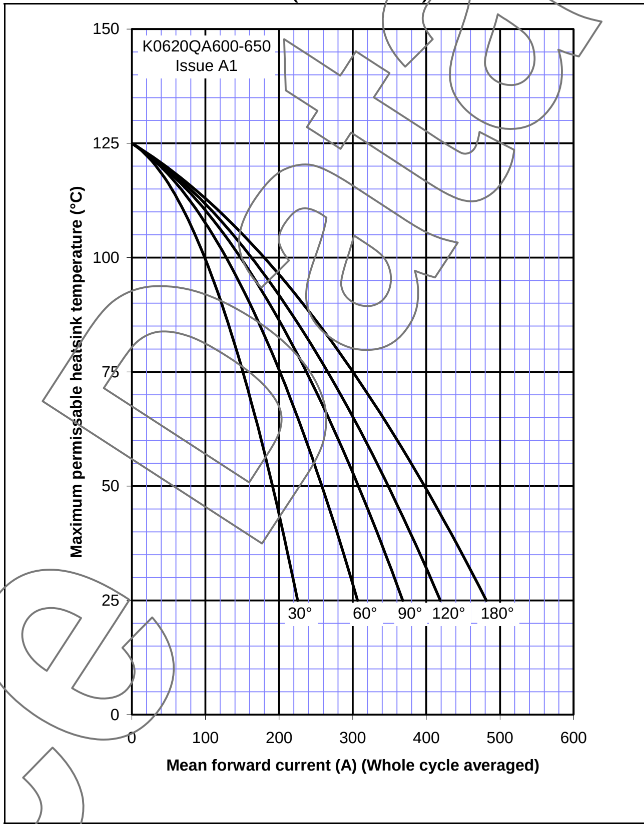


Figure 15 – On-state current vs. Power dissipation – Cathode Side Cooled (Square wave)

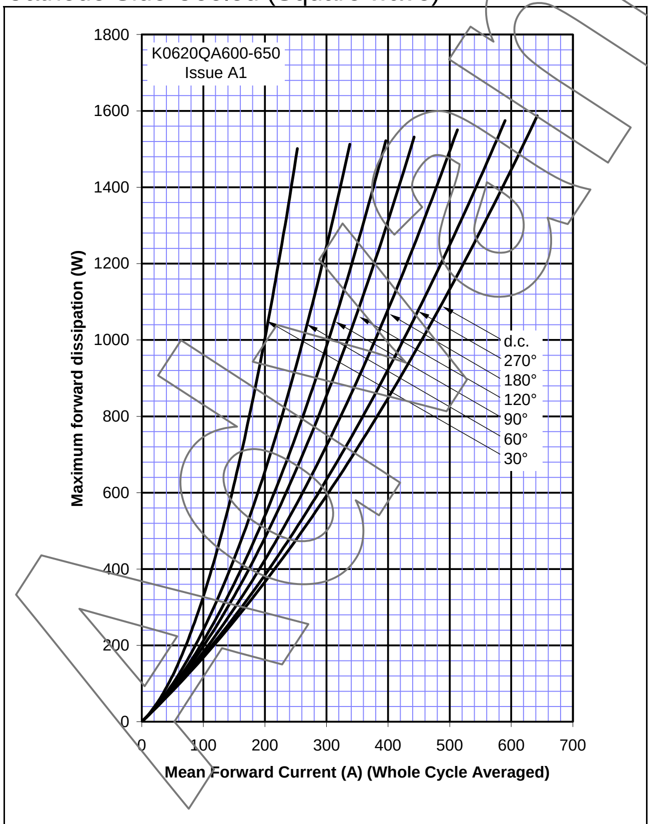


Figure 16 – On-state current vs. Heatsink temperature – Cathode Side Cooled (Square wave)

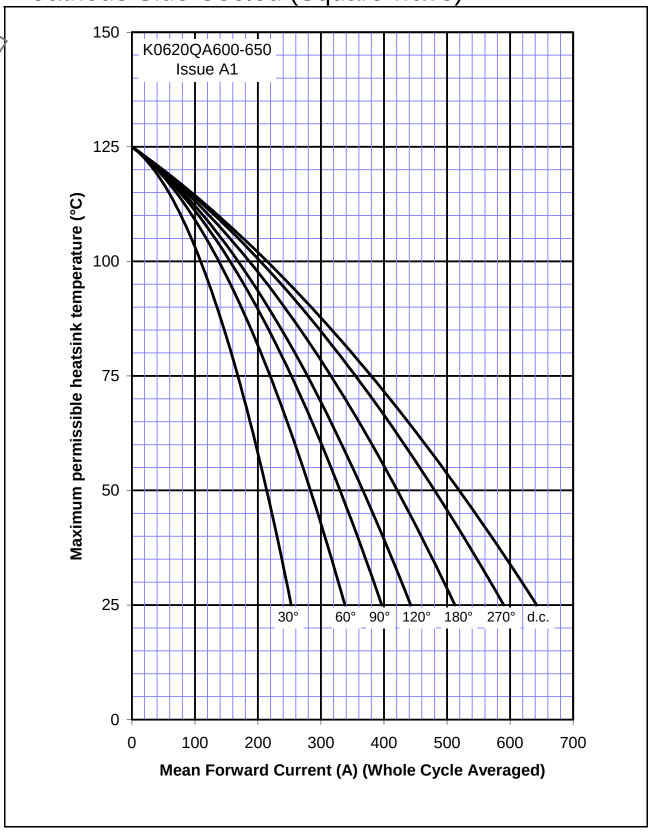


Figure 17 – Square Wave Frequency Ratings

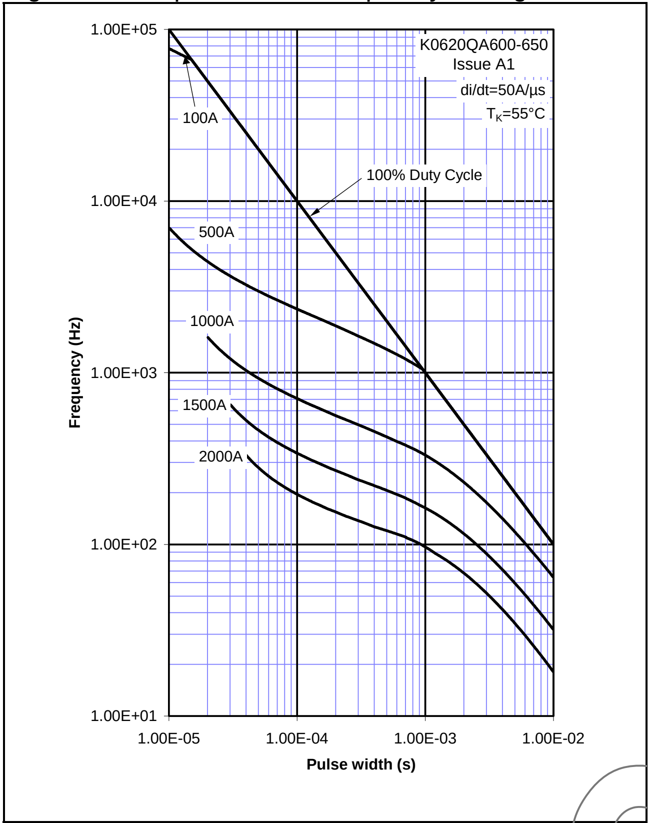


Figure 18 – Sine Wave Frequency Ratings

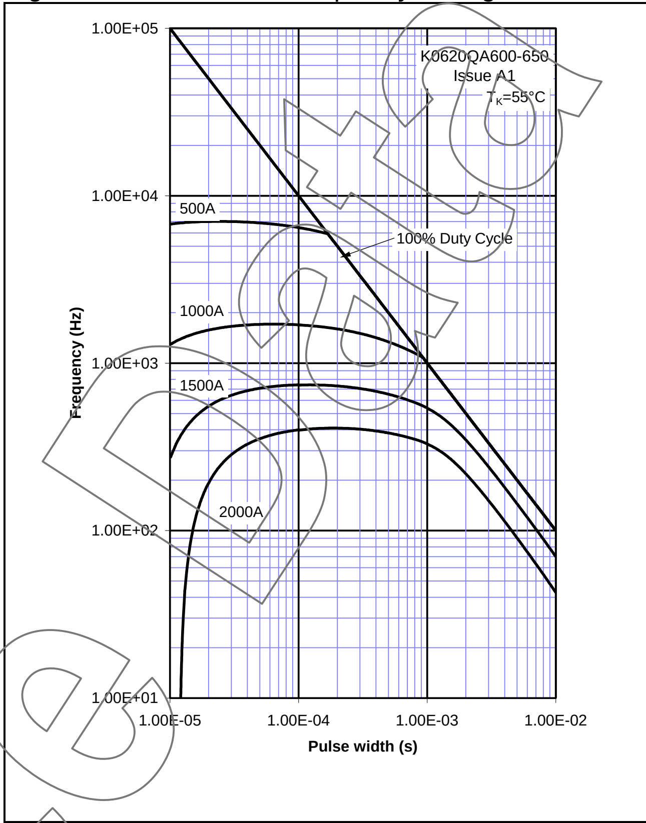
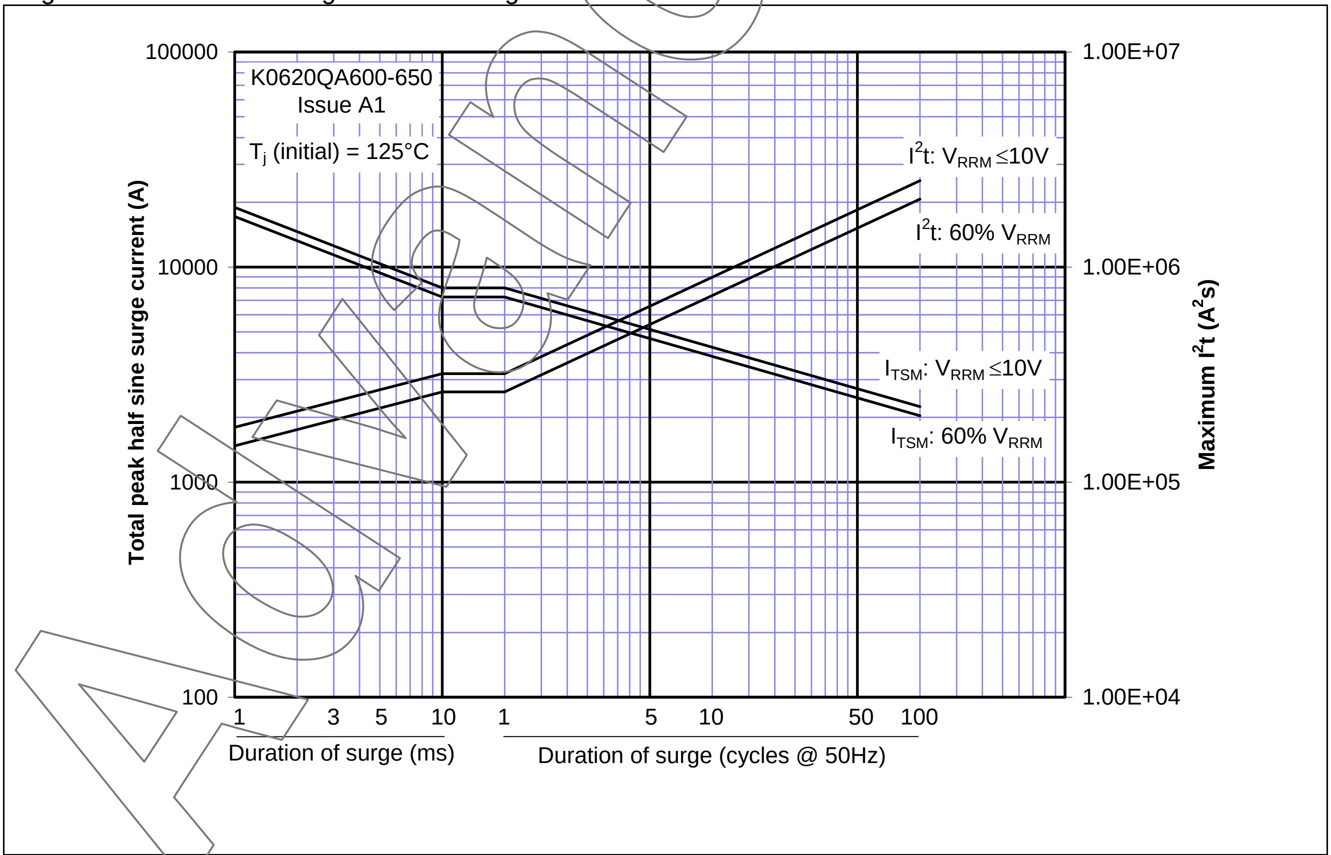
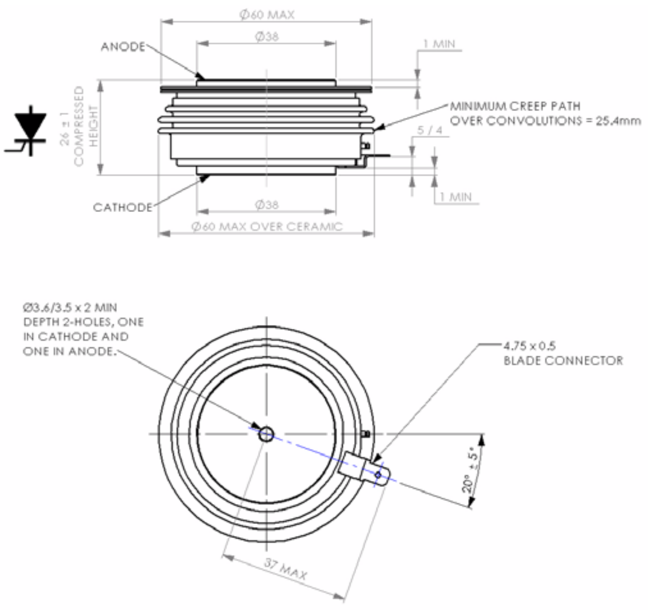


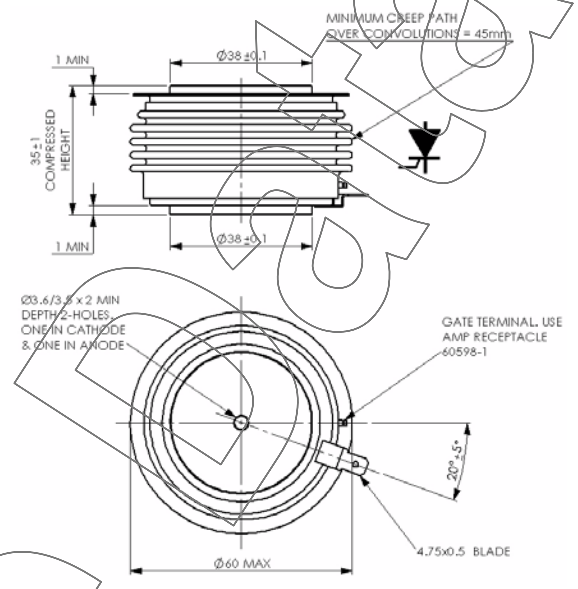
Figure 19 – Maximum surge and I^2t Ratings



Outline Drawing & Ordering Information



Outline option QA



Outline option QE

ORDERING INFORMATION		(Please quote 10 digit code as below)	
K0620	**Q#**	**♦♦**	**0**
Fixed Type Code	Outline Code QA=26mm QE=35mm	Voltage code V_{RRM}/100 60-65	Fixed code

Typical order code: K0620QA650 – 6500V V_{DRM}, V_{RRM}, 26mm clamp height capsule.

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